DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I declare that:

My residence, post office address, and citizenship are as stated below next to my name. I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first, and joint inventor (if plural names are listed below) of the subject matter that is claimed and for which a patent is sought on the invention entitled

SILICON ANNEALED WAFER AND SILICON EPITAXIAL WAFER

the specification of which is atta was filed on amended on		ion Serial No.	, and (if applicable) was
I hereby state that I have reviewed and under referred to above.	erstand the contents of the above iden	ntified specification, including the claims,	as amended by any amendment
I acknowledge the duty to disclose informat 37 CFR §1.56.	ion of which I am aware and which i	s material to the examination of the pater	t application in accordance with
I hereby claim foreign priority benefits under any PCT International application which d checking the space, any foreign application application on which priority is not claimed.	esignates at least one country other	than the United States, listed below and	have also identified below, by
Prior Foreign Application(s)			
Number	Country	Day/Month/Year Filed	Priority Not Claimed
2003-097665	JAPAN	01/04/2003	
I hereby claim the benefit under 35 U.S.C. §	119(e) of any United States provisions	al application(s) listed below.	
Application Serial Number		Filing Date	
to the patentability as defined in 37 CFR §1. filing date of this application. Application Serial Number	Filing Date	Status (patented, pending, ab	
Each undersigned applicant hereby appoint 33,613), as his attorneys with full power of connected therewith.			
Send Correspondence to: CLARK & BRO 835-1755.	DY, 1750 K Street, NW, Suite 600,	Washington, DC 20006; Telephone:	202-835-1111; Facsimile: 202-
I hereby declare that all statements made herein that these statements were made with the knowle of Title 18 of the United States Code and that su	edge that willful false statements and the I	ike so made are punishable by fine or impriso	nment, or both, under Section 1001
Full name of sole or first inventor:	Hideshi NISHIKAWA		
Inventor's signature:	leshi Prishihawa	Date: <u>のン</u> /	102/2004
Citizenship: <u>Japan</u>			* · · · · · · · · · · · · · · · · · · ·
Post Office Address: <u>c/o Sumiton</u>	no Mitsubishi Silicon Corporatio	n, 2-1, Shibaura 1-chome, Minato-l	ku, Tokyo 105-8634 Japan
Full name of second joint inventor, if,	aný:_Nobumitsu TAKASE		
Inventor's signature:	nter Tapases	Date: 02/	02/2004
Residence: Tokyo, Japan	7		
Citizenship: Japan	Miles I Company	0.4.017	T. 107.000 :
Post Office Address: <u>c/o Sumitomo</u>	Mitsubishi Silicon Corporation,	2-1, Shibaura 1-chome, Minato-ku	, Tokyo 105-8634 Japan
	X third and subsequent joint inve	ntors are listed on second sheet	

Full name of third joint inventor, if any: Kazuyuki EGASHIRA	
Inventor's signature: <u>Hasayaki Esashira</u>	
Residence: Tokyo, Japan	
Citizenship: Japan	
Post Office Address: c/o Sumitomo Mitsubishi Silicon Corporation,	2-1, Shibaura 1-chome, Minato-ku, Tokyo 105-8634 Japan
Tull name of fourth is in the contact of any Ulimate LIAVALANA	
Full name of fourth joint inventor, if any: Hiroshi HAYAKAWA	, ,
Inventor's signature: Ttroohi Hayakawa	Date: 02/02/2004
Residence: Tokyo, Japan	
Citizenship: Japan	
Post Office Address: <u>c/o Sumitomo Mitsubishi Silicon Corporation</u>	1, 2-1, Shibaura 1-chome, Minato-ku, Tokyo 105-8634 Japan
Full name of fifth joint inventor, if any:	
Inventor's signature:	Date:
Residence:	
Citizenship:	
Post Office Address:	
Full name of sixth joint inventor, if any:	
Inventor's signature:	Date:
Residence:	
Citizenship:	
Post Office Address:	